

**CMOS**
**Quad Exclusive-OR Gate**
**High-Voltage Types (20-Volt Rating)**

■ CD4030B types consist of four independent Exclusive-OR gates. The CD4030B provides the system designer with a means for direct implementation of the Exclusive-OR function.

The CD4030B types are supplied in 14-lead hermetic dual-in-line ceramic packages (F3A suffix), 14-lead dual-in-line plastic packages (E suffix), 14-lead small-outline packages (M, MT, M96, and NSR suffixes), and 14-lead thin shrink small-outline packages (PW and PWR suffixes).

**MAXIMUM RATINGS, Absolute-Maximum Values:**
**DC SUPPLY-VOLTAGE RANGE, ( $V_{DD}$ )**

Voltages referenced to  $V_{SS}$  Terminal) ..... -0.5V to +20V

**INPUT VOLTAGE RANGE, ALL INPUTS** ..... -0.5V to  $V_{DD}$  +0.5V

**DC INPUT CURRENT, ANY ONE INPUT** .....  $\pm 10\text{mA}$

**POWER DISSIPATION PER PACKAGE (PD):**

For  $T_A = -55^\circ\text{C}$  to  $+100^\circ\text{C}$  ..... 500mW

For  $T_A = +100^\circ\text{C}$  to  $+125^\circ\text{C}$  ..... Derate Linearity at 12mW/ $^\circ\text{C}$  to 200mW

**DEVICE DISSIPATION PER OUTPUT TRANSISTOR**

FOR  $T_A$  = FULL PACKAGE-TEMPERATURE RANGE (All Package Types) ..... 100mW

**OPERATING-TEMPERATURE RANGE ( $T_A$ )** ..... -55 $^\circ\text{C}$  to  $+125^\circ\text{C}$

**STORAGE TEMPERATURE RANGE ( $T_{stg}$ )** ..... -65 $^\circ\text{C}$  to  $+150^\circ\text{C}$

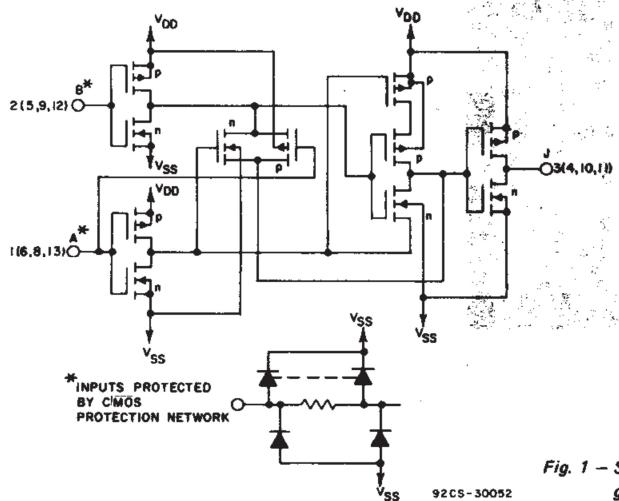
**LEAD TEMPERATURE (DURING SOLDERING):**

At distance 1/16  $\pm$  1/32 inch (1.59  $\pm$  0.79mm) from case for 10s max .....  $+265^\circ\text{C}$

**RECOMMENDED OPERATING CONDITIONS**

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIMITS		UNITS
	MIN.	MAX.	
Supply-Voltage Range (For $T_A$ = Full Package Temperature Range)	3	18	V


**Features:**

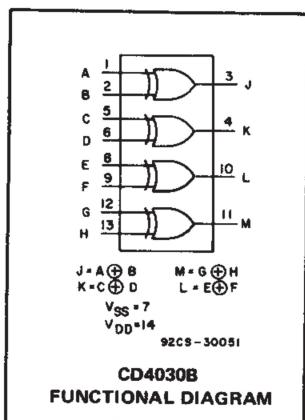
- Medium-speed operation— $t_{PHL}$ ,  $t_{PLH}$  = 65 ns (typ.) at  $V_{DD} = 10\text{V}$ ,  $C_L = 50\text{pF}$
- 100% tested for quiescent current at 20V
- Standardized, symmetrical output characteristics
- 5-V, 10-V, and 15-V parametric ratings
- Maximum input current of 1  $\mu\text{A}$  at 18V over full package-temperature range; 100 nA at 18V and  $25^\circ\text{C}$
- Noise margin (over full package-temperature range):

$$1\text{V at } V_{DD} = 5\text{V}$$

$$2\text{V at } V_{DD} = 10\text{V}$$

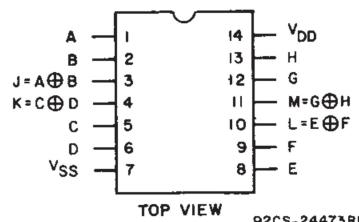
$$2.5\text{V at } V_{DD} = 15\text{V}$$

- Meets all requirements of JEDEC Tentative Standard No. 13B, "Standard Specifications for Description of 'B' Series CMOS Devices"


**Applications:**

- Even and odd-parity generators and checkers
- Logical comparators
- Adders/subtractors
- General logic functions

TERMINAL DIAGRAM  
Top View



TRUTH TABLE FOR ONE OF FOUR IDENTICAL GATES

A	B	J
0	0	0
1	0	1
0	1	1
1	1	0

I = HIGH LEVEL

O = LOW LEVEL

## CD4030B Types

### STATIC ELECTRICAL CHARACTERISTICS

CHARAC-TERISTIC	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C)								UNITS	
	$V_O$ (V)	$V_{IN}$ (V)	$V_{DD}$ (V)	-55	-40	+85	+125	+25			Min.	Typ.	
Quiescent Device Current, $I_{DD}$ Max.	-	0,5	5	0,25	0,25	7,5	7,5	—	0,01	0,25	$\mu A$		
	-	0,10	10	0,5	0,5	15	15	—	0,01	0,5			
	-	0,15	15	1	1	30	30	—	0,01	1			
	-	0,20	20	5	5	150	150	—	0,02	5			
Output Low (Sink) Current $I_{OL}$ Min.	0,4	0,5	5	0,64	0,61	0,42	0,36	0,51	1	—	$mA$		
	0,5	0,10	10	1,6	1,5	1,1	0,9	1,3	2,6	—			
	1,5	0,15	15	4,2	4	2,8	2,4	3,4	6,8	—			
Output High (Source) Current, $I_{OH}$ Min.	4,6	0,5	5	-0,64	-0,61	-0,42	-0,36	-0,51	-1	—	$mA$		
	2,5	0,5	5	-2	-1,8	-1,3	-1,15	-1,6	-3,2	—			
	9,5	0,10	10	-1,6	-1,5	-1,1	-0,9	-1,3	-2,6	—			
	13,5	0,15	15	-4,2	-4	-2,8	-2,4	-3,4	-6,8	—			
Output Voltage: Low-Level, $V_{OL}$ Max.	—	0,5	5	0,05				—	0	0,05	$V$		
	—	0,10	10	0,05				—	—	0,05			
	—	0,15	15	0,05				—	0	0,05			
Output Voltage: High-Level, $V_{OH}$ Min.	—	0,5	5	4,95				4,95	5	—	$V$		
	—	0,10	10	9,95				9,95	10	—			
	—	0,15	15	14,95				14,95	15	—			
Input Low Voltage, $V_{IL}$ Max.	0,5,4,5	—	5	1,5				—	—	1,5	$V$		
	1,9	—	10	3				—	—	3			
	1,5,13,5	—	15	4				—	—	4			
Input High Voltage, $V_{IH}$ Min.	0,5,4,5	—	5	3,5				3,5	—	—	$V$		
	1,9	—	10	7				7	—	—			
	1,5,13,5	—	15	11				11	—	—			
Input Current $I_{IN}$ Max.	—	0,18	18	$\pm 0,1$	$\pm 0,1$	$\pm 1$	$\pm 1$	—	$\pm 10^{-5}$	$\pm 0,1$	$\mu A$		

DYNAMIC ELECTRICAL CHARACTERISTICS at  $T_A = 25^\circ C$ ; Input  $t_r, t_f = 20$  ns,  
 $C_L = 50$  pF,  $R_L = 200$  k $\Omega$

CHARACTERISTIC	CONDITIONS			LIMITS		UNITS	
	$V_{DD}$ (V)	Typ.	Max.				
Propagation Delay Time, $t_{PLH}, t_{PHL}$	5	140	280	$ns$			
	10	65	130				
	15	50	100				
Transition Time, $t_{THL}, t_{TLH}$	5	100	200	$ns$			
	10	50	100				
	15	40	80				
Input Capacitance, $C_{IN}$	Any Input	5	7,5	$pF$			

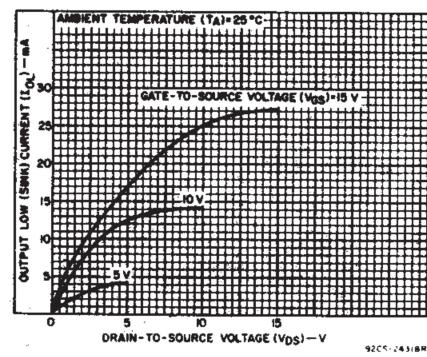


Fig. 2 – Typical output low (sink) current characteristics.

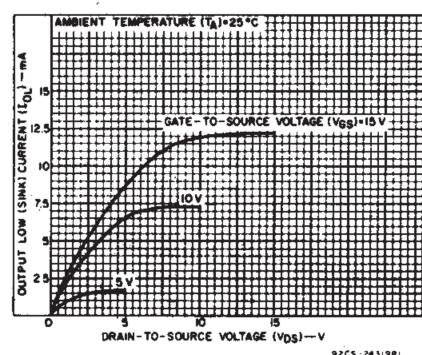


Fig. 3 – Minimum output low (sink) current characteristics.

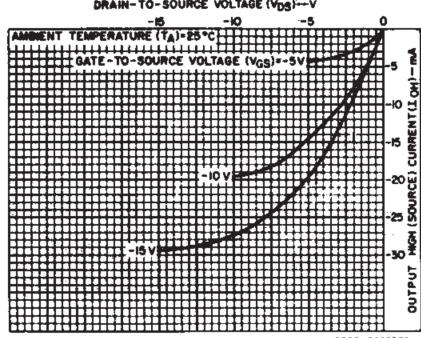


Fig. 4 – Typical output high (source) current characteristics.

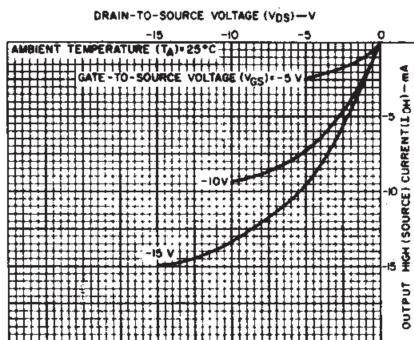


Fig. 5 – Minimum output high (source) current characteristics.

## CD4030B Types

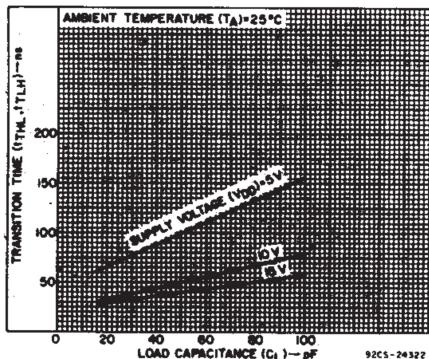


Fig. 6 – Typical transition time as a function of load capacitance.

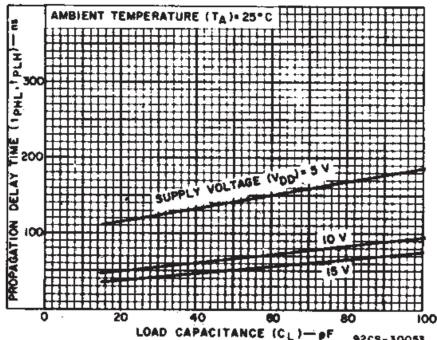


Fig. 7 – Typical propagation delay time as a function of load capacitance.

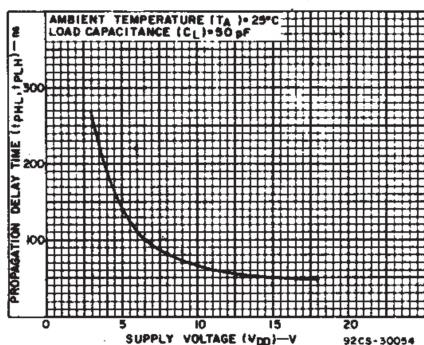


Fig. 8 – Typical propagation delay time as a function of supply voltage.

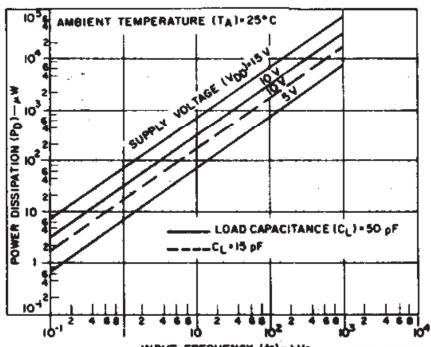


Fig. 9 – Typical dynamic power dissipation as a function of input frequency.

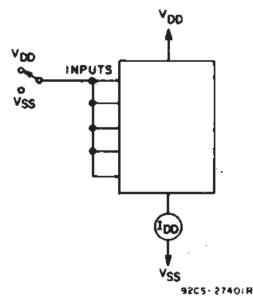


Fig. 10 – Quiescent-device current test circuit.

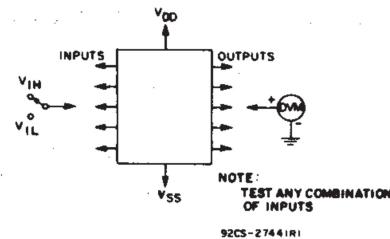


Fig. 11 – Input-voltage test circuit.

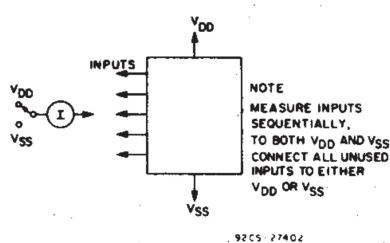


Fig. 12 – Input-current test circuit.

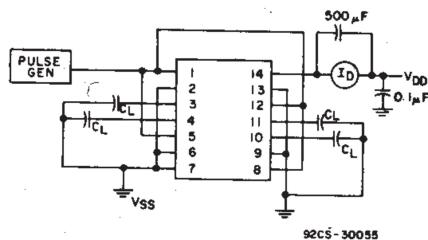
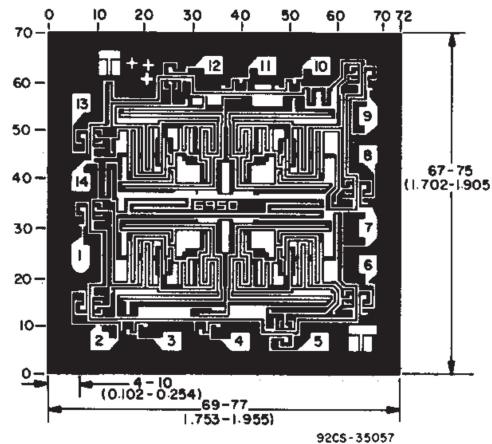


Fig. 13 – Dynamic power dissipation test circuit.



Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils ( $10^{-3}$  inch).